

SPTECH Silicon NPN Power Transistor

2SC3710

DESCRIPTION

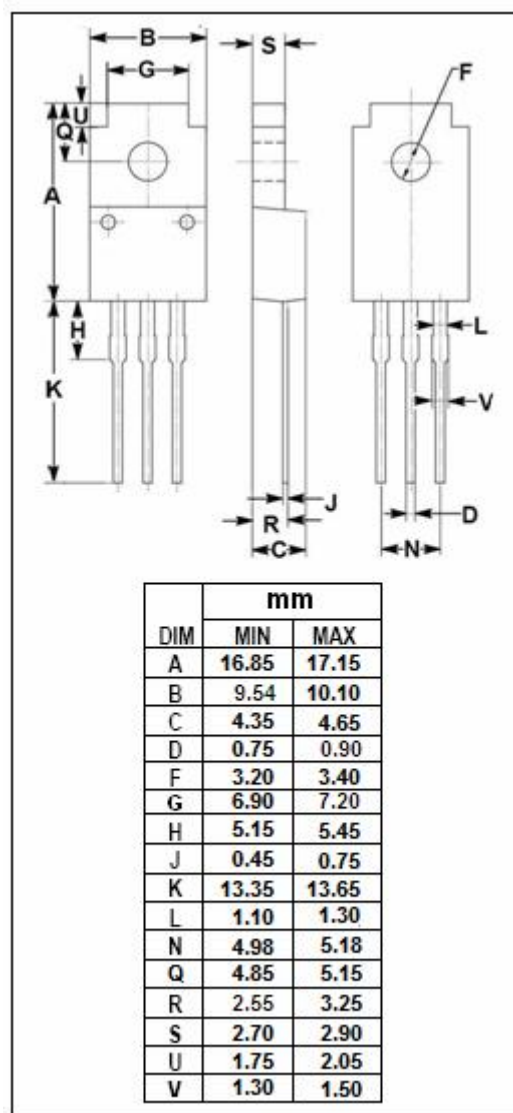
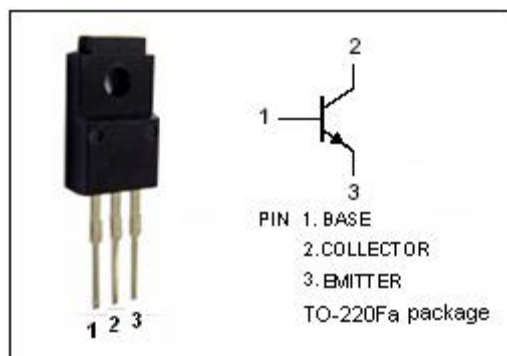
- Low Collector Saturation Voltage-
: $V_{CE(sat)} = 0.4V(\text{Max}) @ I_C = 6A$
- Good Linearity of h_{FE}
- High Switching Speed
- Complement to Type 2SA1452

APPLICATIONS

- Designed for high current switching applications

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	80	V
V_{CEO}	Collector-Emitter Voltage	80	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	12	A
I_B	Base Current-Continuous	2	A
P_C	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	30	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$



SPTECH Silicon NPN Power Transistor

2SC3710

ELECTRICAL CHARACTERISTICS

 $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=50\text{mA}$; $I_B=0$	80			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=6\text{A}$; $I_B=0.3\text{A}$			0.4	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=6\text{A}$; $I_B=0.3\text{A}$			1.2	V
I_{CBO}	Collector Cutoff Current	$V_{CB}=80\text{V}$; $I_E=0$			10	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=6\text{V}$; $I_C=0$			10	μA
h_{FE-1}	DC Current Gain	$I_C=1\text{A}$; $V_{CE}=1\text{V}$	70		240	
h_{FE-2}	DC Current Gain	$I_C=6\text{A}$; $V_{CE}=1\text{V}$	40			
C_{OB}	Output Capacitance	$I_E=0$; $V_{CB}=10\text{V}$; $f_{\text{test}}=1\text{MHz}$		220		pF
f_T	Current-Gain—Bandwidth Product	$I_C=1\text{A}$; $V_{CE}=5\text{V}$		80		MHz

Switching Times

t_{on}	Turn-on Time	$I_C=6\text{A}$, $I_{B1}=-I_{B2}=0.3\text{A}$, $V_{CC}=30\text{V}$, $R_L=5\Omega$		0.2		μs
t_{stg}	Storage Time			1.0		μs
t_f	Fall Time			0.2		μs

◆ h_{FE-1} Classifications

O	Y
70-140	120-240